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# (54) SWITCHING OSCILLATION REDUCTION FOR POWER SEMICONDUCTOR DEVICE MODULES

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#### (57) ABSTRACT

In a general aspect, a half-bridge circuit includes a substrate having first, second and third patterned metal layers disposed on a surface. The circuit also includes first and second high-side transistors disposed on the first patterned metal layer, and first and conductive clips electrically coupling, respectively, the first and second high-side transistors with the second patterned metal layer. The circuit also includes first and second low-side transistors disposed on the second patterned metal layer, and third and fourth conductive clips electrically coupling, respectively, the first and second lowside transistors with the third patterned metal layer. The circuit further includes a DC+ terminal electrically coupled with the first patterned metal layer via a first conductive post disposed between the first and second high-side transistors, and a DC- terminal electrically coupled with the third patterned metal layer via a second conductive post disposed between the third and fourth conductive clips.

